

Appl. No. 10/530,063; Docket No. BE02 0027US
Amdt. dated November 15, 2005
Response to Notice of Non-Compliant Amendment of 08-NOV-2005

Amendments to the Claims

1. (*Original*) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition, and including employing nitrogen or a noble gas as a carrier gas.
2. (*Original*) A method as claimed in claim 1, which is employed to form an epitaxial layer based on silicon, germanium and/or carbon.
3. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-y}\text{C}_y$.
4. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a SiGe epitaxial layer.
5. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$.
6. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a silicon epitaxial layer.
7. (*Original*) A method as claimed in any one of the preceding claims, which is carried out at a low temperature.
8. (*Original*) A method as claimed in claim 7, which is carried out at a temperature of less than about 600°C.
9. (*Currently Amended*) Chemical Vapor Deposition apparatus (10) comprising a chamber (12) having a gas input port (14) and a gas output port (16), and means (18) for mounting a silicon substrate (20) within the chamber (12), said apparatus (10) further including a gas source (24) connected to the input port (14) and arranged to provide nitrogen or a noble gas as a carrier gas.

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10. (*Currently Amended*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in ~~any one of claims 2-8~~
claim 2.
11. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 3.
12. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 4.
13. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 5.
14. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 6.
15. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 7.
16. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 8.